2N5356

SILICON PNP TRANSISTOR



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DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2N5356 is a silicon PNP transistor, manufactured by the epitaxial planar process, designed for general purpose amplifier and switching applications.





MAXIMUM RATINGS: (T _A =25°C)	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	25	V
Collector-Emitter Voltage	VCEO	25	V
Emitter-Base Voltage	V_{EBO}	4.0	V
Continuous Collector Current	IC	350	mA
Peak Collector Current	I _{CM}	700	mA
Power Dissipation	P_{D}	360	mW
Operating and Storage Junction Temperature	T _J , T _{stg}	-65 to +150	°C

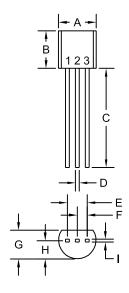
Storage Junction Temperature	^I J ^{, I} stg	-65 to +150		30
CHARACTERISTICS: (TA=25°C u	ınless otherwise	noted)		
TEST CONDITIONS	MIN	TYP	MAX	UNITS
				nA
OB · //			10	μA
V _{CE} =25V			100	nA
V _{EB} =4.0V			10	μΑ
I _C =10mA	25			V
I _C =50mA, I _B =2.5mA			250	mV
I _C =300mA, I _B =30mA			1.0	V
I _C =50mA, I _B =2.5mA			1.1	V
I_C =300mA, I_B =30mA			2.0	V
V_{CE} =10V, I_{C} =2.0mA	500		800	mV
V_{CE} =10V, I_{C} =2.0mA	200			
V_{CE} =1.0V, I_{C} =50mA	250		500	
V_{CE} =5.0V, I_{C} =300mA	75			
V_{CE} =10V, I_{C} =2.0mA, f=1.0kHz	200		750	
V_{CE} =10V, I_{C} =2.0mA		250		MHz
V_{CB} =10V, I_E =0, f=1.0MHz			8.0	pF
V_{EB} =0.5V, I_{C} =0, f=1.0MHz			35	pF
	CHARACTERISTICS: (T _A =25°C to TEST CONDITIONS V _{CB} =25V V _{CB} =25V V _{CB} =25V V _{EB} =4.0V I _C =10mA I _C =50mA, I _B =2.5mA I _C =300mA, I _B =30mA I _C =50mA, I _B =2.5mA I _C =300mA, I _B =2.5mA I _C =300mA, I _C =300mA V _{CE} =10V, I _C =2.0mA V _{CE} =10V, I _C =2.0mA V _{CE} =1.0V, I _C =50mA V _{CE} =5.0V, I _C =300mA V _{CE} =10V, I _C =2.0mA, f=1.0kHz V _{CE} =10V, I _C =2.0mA	CHARACTERISTICS: (T _A =25°C unless otherwise TEST CONDITIONS V _{CB} =25V V _{CB} =25V (T _A =100°C) V _{CE} =25V V _{EB} =4.0V I _C =10mA 25 I _C =50mA, I _B =2.5mA I _C =300mA, I _B =30mA I _C =300mA, I _B =30mA I _C =300mA, I _B =2.5mA I _C =300mA, I _C =2.0mA 500 V _{CE} =10V, I _C =2.0mA 200 V _{CE} =10V, I _C =2.0mA 200 V _{CE} =1.0V, I _C =50mA 250 V _{CE} =5.0V, I _C =300mA 75 V _{CE} =10V, I _C =2.0mA 200 V _{CE} =10V, I _C =2.0mA 200 V _{CE} =10V, I _C =2.0mA 75 V _{CE} =10V, I _C =2.0mA 100 V _{CE} =10V	CHARACTERISTICS: (T _A =25°C unless otherwise noted) TEST CONDITIONS WIN V _{CB} =25V V _{CB} =25V V _{CE} =25V V _{EB} =4.0V I _C =10mA I _C =50mA, I _B =2.5mA I _C =300mA, I _B =30mA I _C =50mA, I _B =2.5mA I _C =300mA, I _B =2.5mA I _C =300mA, I _C =2.0mA I _C =10V, I _C =2.0mA V _{CE} =10V, I _C =2.0mA V _{CE} =10V, I _C =2.0mA V _{CE} =1.0V, I _C =50mA V _{CE} =5.0V, I _C =300mA V _{CE} =10V, I _C =2.0mA CE=10V, I _C =2.0mA CE=10V, I _C =2.0mA	CHARACTERISTICS: (T _A =25°C unless otherwise noted) TEST CONDITIONS V _{CB} =25V V _{CB} =25V V _{CE} =25V 100 V _{CE} =10MA 25 I _C =50mA, I _B =2.5mA 250 I _C =50mA, I _B =30mA 1.0 I _C =50mA, I _B =2.5mA 1.1 I _C =300mA, I _B =30mA 2.0 V _{CE} =10V, I _C =2.0mA 200 V _{CE} =10V, I _C =2.0mA 200 V _{CE} =10V, I _C =2.0mA 250 V _{CE} =10V, I _C =300mA 75 V _{CE} =10V, I _C =2.0mA 250 V _{CE} =10V, I _C =2.0mA

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TO-92 CASE - MECHANICAL OUTLINE



DIMENSIONS						
	INCHES		MILLIMETERS			
SYMBOL	MIN	MAX	MIN	MAX		
A (DIA)	0.175	0.205	4.45	5.21		
В	0.170	0.210	4.32	5.33		
С	0.500	-	12.70	-		
D	0.016	0.022	0.41	0.56		
E	0.100		2.54			
F	0.050		1.27			
G	0.125	0.165	3.18	4.19		
Н	0.080	0.105	2.03	2.67		
	0.015		0.38			

TO-92 (REV: R1)

LEAD CODE:

- 1) Emitter 2) Collector 3) Base

R1

MARKING:

FULL PART NUMBER

OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- · Inventory bonding
- · Consolidated shipping options

- · Custom bar coding for shipments
- · Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free guick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- · Custom electrical curves
- · Environmental regulation compliance
- · Customer specific screening
- · Up-screening capabilities

- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- · Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

- 1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
- 2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

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